EYP-DFB-0760-00010-1500-BFY02-0x0x

eagleyard PHOTONICS

We focus on power.

DISTRIBUTED FEEDBACK LASER
GaAs Semiconductor Laser Diode
with integrated grating structure

RWE/RWL   BAL   DFB/DBR   TPL/TPA

General Product Information

Product	Application
760 nm DFB Laser with hermetic Butterfly Housing	Spectroscopy
Monitor Diode, Thermoelectric Cooler and Thermistor	O_2 Detection
PM Fiber with angle-polished Connector	Metrology
High-reliable Package compliant for Space Applications	

Absolute Maximum Ratings

	Symbol	Unit	min	typ	max
Storage Temperature	T_S	°C	-40		85
Operational Temperature at Case	T_C	°C	-40		85
Operational Temperature at Laser Chip	T_{LD}	°C	10		50
Forward Current	I_F	mA			130
Reverse Voltage	V_R	V			2
Output Power	P_{opt}	mW			12
TEC Current	I_{TEC}	A			1.8
TEC Voltage	V_{TEC}	V			3.2

Stress in excess of the Absolute Maximum Ratings can cause permanent damage to the device.

Recommended Operational Conditions

	Symbol	Unit	min	typ	max	Measurement Conditions / Comments
Operational Temperature at Case	T_C	°C	-20		65	
Operational Temperature at Laser Chip	T_{LD}	°C	15		35	measured by integrated Thermistor
Forward Current	I_F	mA			120	
Output Power	P_{opt}	mW	2		10	ex fiber

Characteristics at T_{LD} = 25 °C at Begin Of Life

Parameter	Symbol	Unit	min	typ	max	Measurement Conditions / Comments
Center Wavelength	λ_C	nm	759	760	761	see images on page 4
Spectral Width (FWHM)	$\Delta\nu$	MHz		2		
Temperature Coefficient of Wavelength	$d\lambda / dT$	nm / K		0.06		
Current Coefficient of Wavelength	$d\lambda / dI$	nm / mA		0.003		
Output Power @ I_F = 120 mA	P_{opt}	mW	10			ex fiber

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Characteristics at T_{LD} = 25 °C at Begin Of Life   cont'd

Parameter	Symbol	Unit	min	typ	max	Measurement Conditions / Comments
Slope Efficiency	S	W / A	0.1	0.2	0.3	
Threshold Current	I_{th}	mA			70	
Polarization Extinction Ratio	PER	dB		10		P_{opt} = 10 mW
Sidemode Supression Ratio	SMSR	dB	30	45		see below
Mode-hop free Operating Range (SMSR > 30 dB)						
▸ Variant 0 (see order code scheme)	T_{LD}	° C		25		temperature measured by integrated themistor
	P_{opt}	mW		10		
▸ Variant 2 (see order code scheme)	T_{LD}	° C	15		35	temperature measured by integrated themistor
	P_{opt}	mW	2		10	

Monitor Diode

Parameter	Symbol	Unit	min	typ	max	Measurement Conditions / Comments
Monitor Detector Responsivity	I_{mon} / P_{opt}	µA/mW	5		200	P_{opt} = 2 … 10 mW, $U_{R\,MD}$ = 5 V

Thermoelectric Cooler

Parameter	Symbol	Unit	min	typ	max	Measurement Conditions / Comments
Current	I_{TEC}	A		0.4		P_{opt} = 10 mW, ΔT = 20 K
Voltage	U_{TEC}	V		0.8		P_{opt} = 10 mW, ΔT = 20 K
Power Dissipation (total loss at case)	P_{loss}	W		0.5		P_{opt} = 10 mW, ΔT = 20 K
Temperature Difference	ΔT	K			50	P_{opt} = 10 mW, ΔT = I T_{case} - T_{LD} I

Thermistor (Standard NTC Type)

Parameter	Symbol	Unit	min	typ	max	Measurement Conditions / Comments
Resistance	R	kΩ		10		
Beta Coefficient	β			3976		

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Fiber and Connector Type

PM Fiber	900 / 125 / 5.5 µm, UV/Polyester-elastomer Coating (l = 1 +/-0.1 m)
Connector	different variants available
	▸ FC/APC (narrow key / 2mm)
	▸ SC/APC
	▸ other types on request

Measurement Conditions / Comments

see order code scheme

Package Pinout

1	Thermoelectric Cooler (+)	14	Thermoelectric Cooler (-)
2	Thermistor	13	Case
3	Photodiode (Anode)	12	not connected
4	Photodiode (Cathode)	11	Laser Diode (Cathode)
5	Thermistor	10	Laser Diode (Anode)
6	not connected	9	not connected
7	not connected	8	not connected

top view
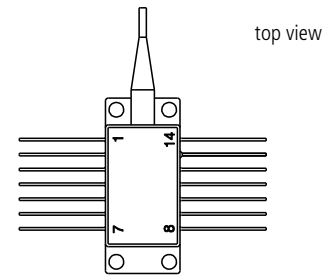
Package Drawings
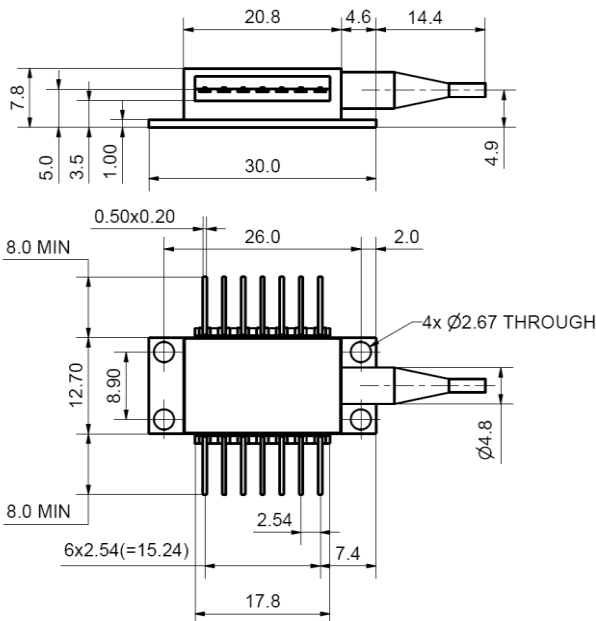
recommended
min. bending radius: 30 mm

4x Ø2.67 THROUGH

Z11-SPEC-BFY02-DFB-0000

PM fiber

connector key
E field
fast axis
slow axis
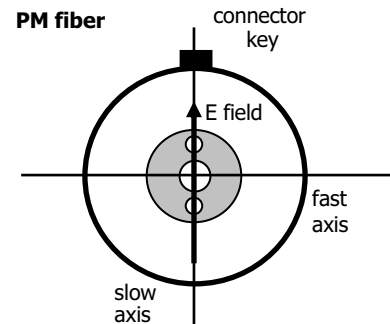
slow axis of the PM fiber aligned to connector key

hermetically sealed Package:
Leak Rate < 5 · 10^{-8} atm.cc./s
acc. MIL-STD-883E

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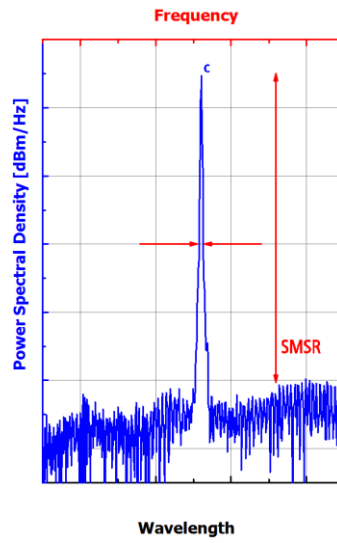RWE/RWL   BAL   DFB/DBR   TPL/TPA

Typical Measurement Results

Output Power vs. Current
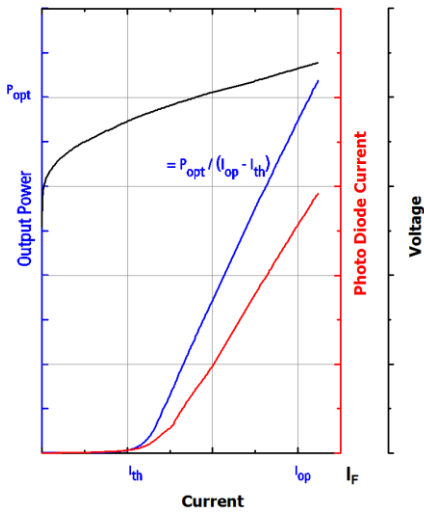
Spectra at Specified Optical Output Power

Performance figures, data and any illustrative material provided in this specification are typical and must be specifically confirmed in writing by eagleyard Photonics before they become applicable to any particular order or contract. In accordance with the eagleyard Photonics policy of continuous improvement specifications may change without notice.

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Order Code Scheme

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Connector

FC/APC (narrow key / 2mm)	0
SC/APC	1
other connector or fiber types upon request	

Mode-hop free Tuning Range (Minimum Side Mode Suppression Ratio > 30 dB)

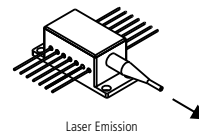|		
$P_{opt} = $ 10 mW;	$T_{LD} = 25°$	Variant 0	0
$P_{opt} = $ 2 … 10 mW;	$T_{LD} = 15 … 35°$	Variant 2	2

Unpacking, Installation and Laser Safety

Unpacking the laser diodes should only be done at electrostatic safe workstations (EPA). Though protection against electro static discharge (ESD) is implemented in the laser package, charges may occur at surfaces. Please store this product in its original package at a dry, clean place until final use. During device installation, ESD protection has to be maintained.

The DFB diode type is known to be sensitive against optical feedback, so an optical isolator may be required in some cases. Operating at moderate temperatures on a proper metal heat sinks willl contribute to stable operation and a long lifetime of the diode.

The laser emission from this diode is close to the invisible infrared region of the electromagnetic spectrum. Avoid direct and/or indirect exposure to the free running beam. Collimating the free running beam with optics as common in optical instruments will increase threat to the human eye.

Each laser diode will come with an individual test protocol verifying the parameters given in this document.

Laser Emission

INVISIBLE LASER RADIATION
AVOID EYE OR SKIN EXPOSURE
TO DIRECT OR SCATTERED RADIATION
CLASS 4 LASER PRODUCT

WAVELENGTH   760 nm
MAX. LASER POWER 12 mW

IEC 60825-1

DANGER
INVISIBLE LASER RADIATION
AVOID EYE OR SKIN EXPOSURE TO
DIRECT OR SCATTERED RADIATION
GaAs SEMICONDUCTOR LASER DIODE
12 mW MAX OUTPUT AT 760 nm
CLASS IV LASER PRODUCT
Complies with 21 CFR 1040.10 and 1040.40

GL
ISM
ISO 9001
GL Systems Certification